ADE-208-209C(Z)

HRW0202A
Silicon Schottky Barrier Diode for Rectifying

HITACHI

Rev. 3
Apr. 1995

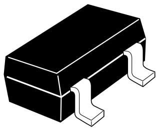
Features

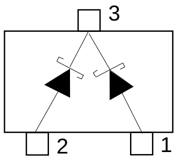
- Low forward voltage drop and suitable for high effifiency rectifying.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HRW0202A	S17	MPAK

Pin Arrangement





(Top View)

1 Anode
2 Anode
3 Cathode

Absolute Maximum Ratings (Ta = 25°C) *

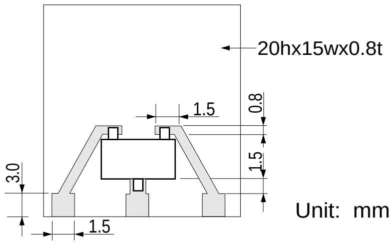
Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}**	20	V
Average forward current	I_o***	200	mA
Non-Repetitive peak forward surge current	I_{FSM}****	3	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

* Per one device
** See Fig.5
*** See Fig.4, Square wave, Duty (1/2), Two device total
**** 10msec half sine wave 1 pulse

Electrical Characteristics (Ta = 25°C) *

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse current	I_R	—	—	50	µA	V_R = 20 V
Forward voltage	V_F	—	—	0.40	V	I_F = 100 mA
Thermal resistance	$R_{th(j-a)}$	—	350	—	°C/W	Polyimide substrate **

* Per one device
** Polyimide PCB



HRW0202A

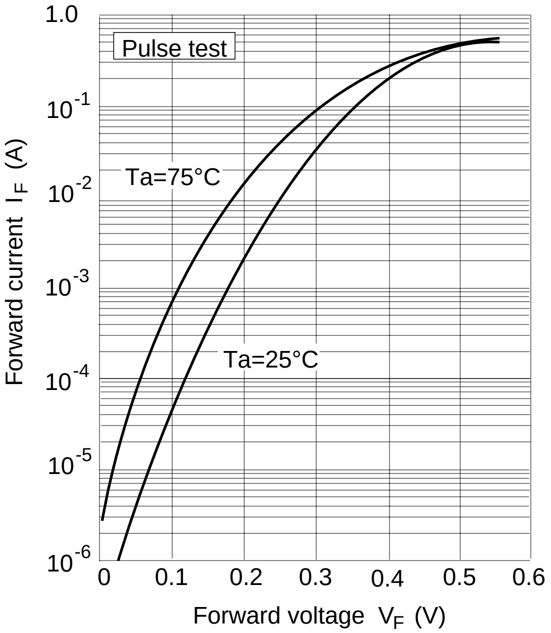


Fig.1 Forward current Vs. Forward voltage

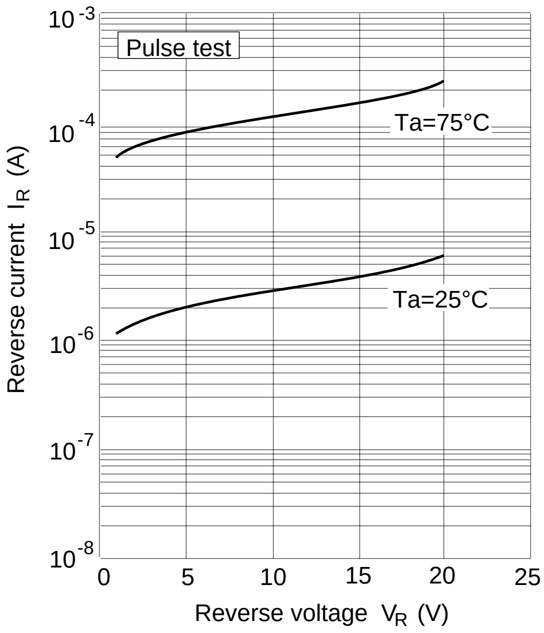


Fig.2 Reverse current Vs. Reverse voltage

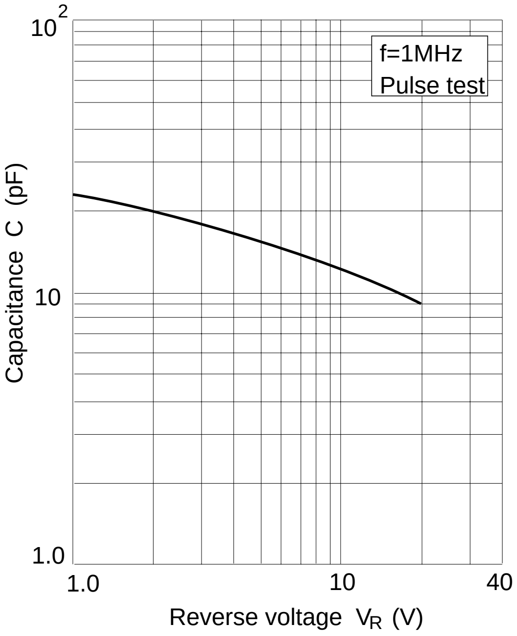


Fig.3 Capacitance Vs. Reverse voltage

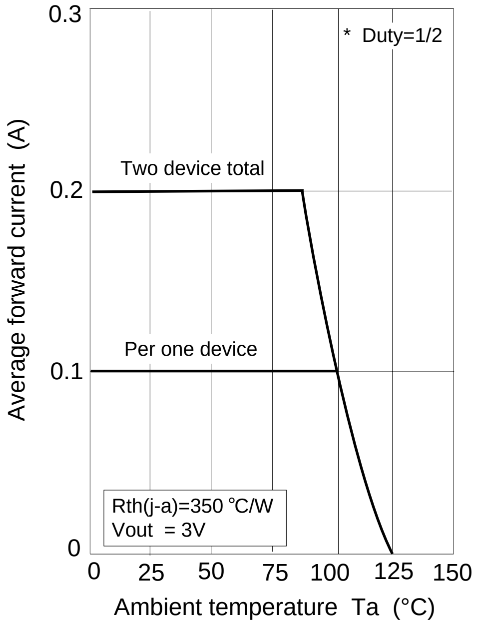


Fig.4 Average forward current Vs. Ambient temperature

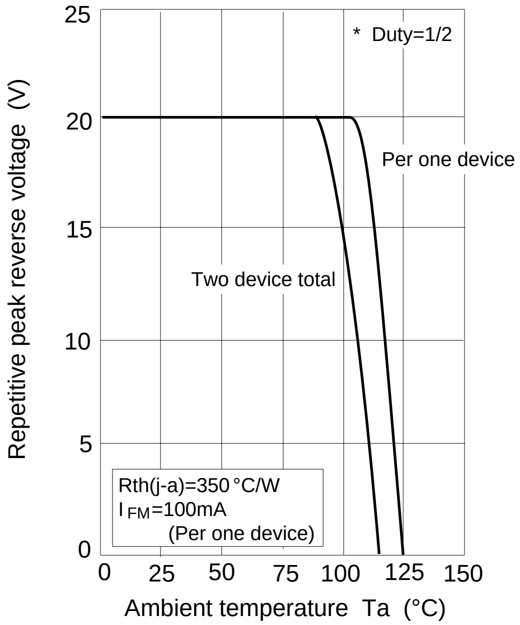
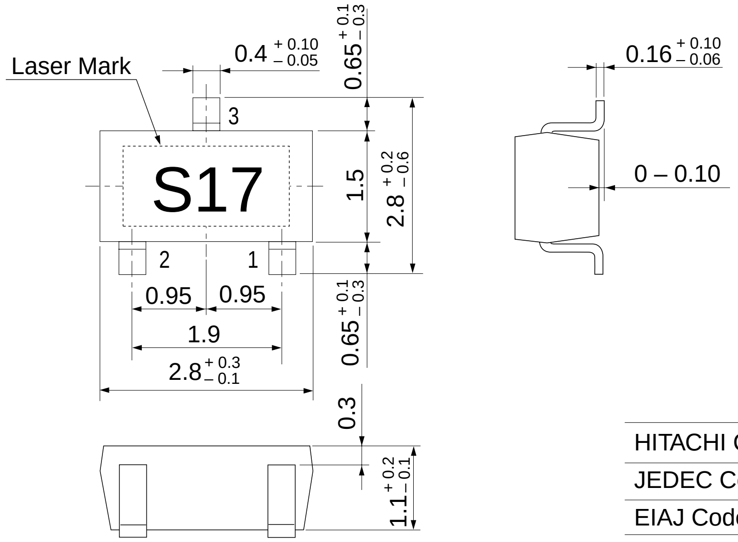


Fig.5 Repetitive peak reverse voltage Vs. Ambient temperature

Package Dimensions

Unit: mm



1 Anode
2 Anode
3 Cathode

HITACHI Code	MPAK(1)
JEDEC Code	—
EIAJ Code	SC-59A
Weight (g)	0.011